

### Small Signal Fast Switching Diodes



#### FEATURES

- Silicon epitaxial planar diodes
- Electrical data are identical with device 1N4148
- AEC-Q101 qualified



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

#### APPLICATIONS

- Extreme fast switches

#### MECHANICAL DATA

**Case:** MiniMELF SOD-80

**Weight:** approx. 31 mg

**Cathode band color:** black

**Packaging codes/options:**

08/2.5K per 7" reel (8 mm tape), 12.5K/box

18/10K per 13" reel (8 mm tape), 10K/box

PARTS TABLE					
PART	TYPE DIFFERENTIATION	ORDERING CODE	TYPE MARKING	INTERNAL CONSTRUCTION	REMARKS
LL4148-M	$V_{RRM} = 100\text{ V}$ , $V_F = \text{max. } 1000\text{ mV at } I_F = 50\text{ mA}$	LL4148-M-08 or LL4148-M-18	-	Single diode	Tape and reel

ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Repetitive peak reverse voltage		$V_{RRM}$	100	V
Reverse voltage		$V_R$	75	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	$I_{FSM}$	2	A
Repetitive peak forward current		$I_{FRM}$	500	mA
Forward continuous current		$I_F$	300	mA
Average forward current	$V_R = 0$	$I_{F(AV)}$	150	mA
Power dissipation <sup>(1)</sup>		$P_{tot}$	500	mW

**Note**

<sup>(1)</sup> Valid provided that electrodes are kept at ambient temperature

THERMAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Thermal resistance junction to ambient air <sup>(1)</sup>		$R_{thJA}$	300	K/W
Junction temperature		$T_j$	175	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

**Note**

<sup>(1)</sup> Valid provided that electrodes are kept at ambient temperature

ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	$V_F$		860	1000	mV
Reverse current	$V_R = 20\text{ V}$	$I_R$			25	nA
	$V_R = 20\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	$I_R$			50	$\mu\text{A}$
Reverse current	$V_R = 75\text{ V}$	$I_R$			5	$\mu\text{A}$
	$I_R = 100\text{ }\mu\text{A}, t_p/T = 0.01,$ $t_p = 0.3\text{ ms}$	$V_{(BR)}$	100			V
Diode capacitance	$V_R = 0\text{ V}, f = 1\text{ MHz},$ $V_{HF} = 50\text{ mV}$	$C_D$			4	pF
Reverse recovery time	$I_F = I_R = 10\text{ mA},$ $i_R = 1\text{ mA}$	$t_{rr}$			8	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V},$ $i_R = 0.1 \times I_R, R_L = 100\text{ }\Omega$				4	

### TYPICAL CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

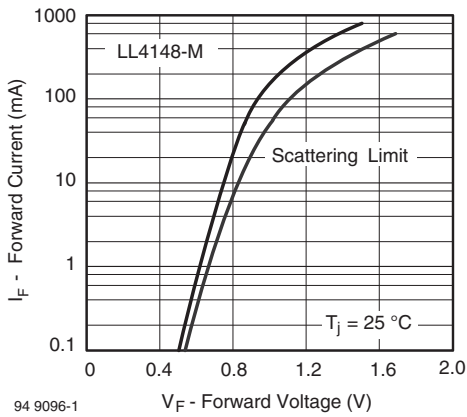


Fig. 1 - Forward Current vs. Forward Voltage

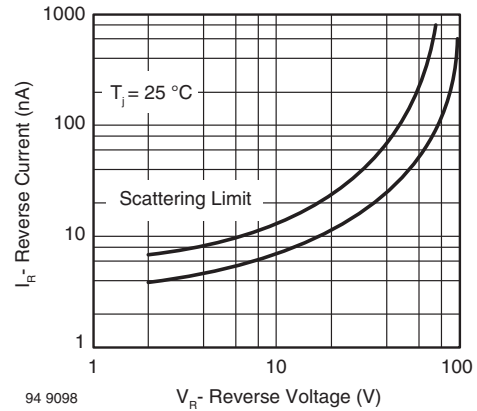


Fig. 3 - Diode Capacitance vs. Reverse Voltage

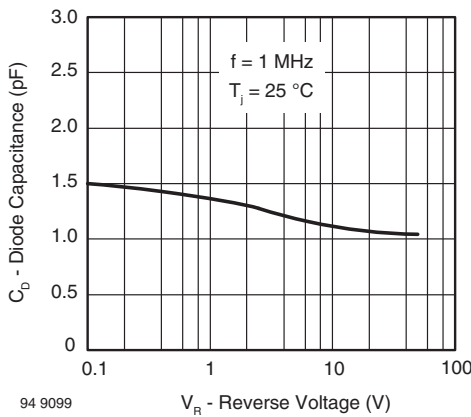
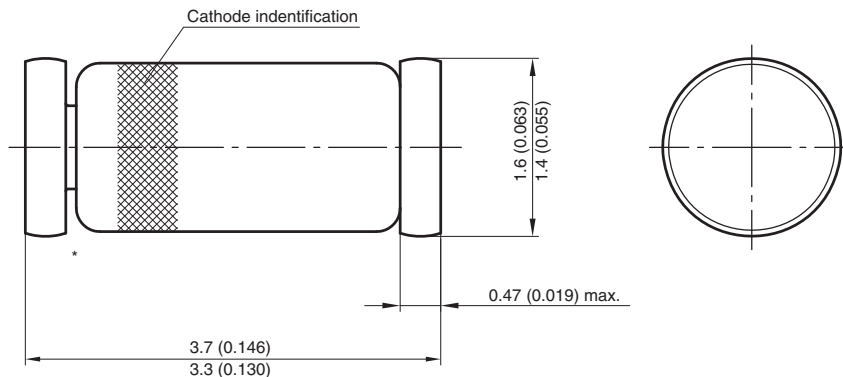
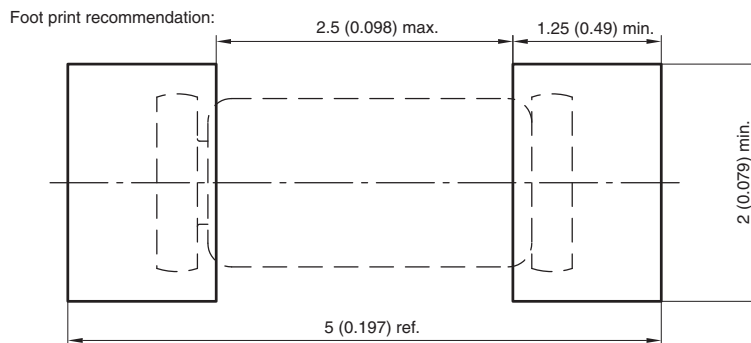


Fig. 2 - Reverse Current vs. Reverse Voltage

**PACKAGE DIMENSIONS** in millimeters (inches): **MiniMELF SOD-80**



\* The gap between plug and glass can be either on cathode or anode side



Document no.:6.560-5005.01-4  
 Rev. 8 - Date: 07.June.2006  
 96 12070